## WE CLAIM:

- 1. A method of forming a programmable conductor memory cell comprising: sputtering metal and chalcogenide glass onto a prepared substrate; and maintaining the prepared substrate at a temperature higher than room temperature during the sputtering.
- 2. The method of Claim 1, wherein sputtering metal and chalcogenide glass comprises first sputtering a chalcogenide glass element and then separately sputtering a metal layer thereover.
- 3. The method of Claim 1, wherein sputtering metal and chalcogenide glass comprises co-sputtering.
- 4. The method of Claim 1, wherein the prepared substrate comprises a top insulating layer with vias therein.
- 5. The method of Claim 1, wherein the programmable conductor memory cell comprises metal and chalcogenide glass containing between about 25% and 35% metal.
  - 6. The method of Claim 1, wherein the metal is a fast diffuser.
  - 7. The method of Claim 1, wherein the metal is silver.
  - 8. The method of Claim 1, wherein the metal is copper.
- 9. The method of Claim 1, wherein the chalcogenide glass comprises components selected from the group consisting of sulfur, germanium, selenium, and tellurium.
- 10. The method of Claim 1, wherein the chalcogenide glass comprises germanium selenide.
- 11. The method of Claim 1, further comprising maintaining the prepared substrate at a temperature higher than room temperature for at least 5 minutes before sputtering the metal and chalcogenide glass.
- 12. The method of Claim 1, wherein maintaining the prepared substrate at a temperature higher than room temperature comprises maintaining the prepared substrate at between about 30°C and 150°C.

- 13. The method of Claim 1, wherein maintaining the prepared substrate at a temperature higher than room temperature comprises maintaining the prepared substrate at between about 45°C and 60°C.
- 14. A method of co-sputtering a homogeneous metal/chalcogenide glass layer onto an irregular surface, comprising keeping the irregular surface at an elevated temperature, above room temperature, before and during the co-sputtering.
- 15. The method of Claim 14, wherein the metal/chalcogenide glass layer comprises silver, germanium, and selenium.